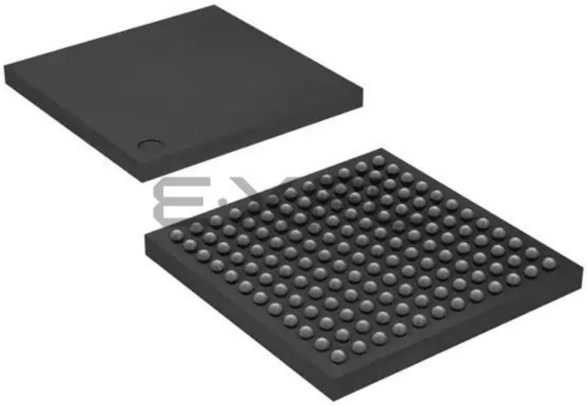

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, SD, SPI, UART/USART
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	104
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 46x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LBGA
Supplier Device Package	144-MAPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dn512zvmd10

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1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers: PK10 and MK10 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
K##	Kinetis family	• K10
A	Key attribute	• D = Cortex-M4 w/ DSP • F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	• N = Program flash only • X = Program flash and FlexMemory

Table continues on the next page...

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

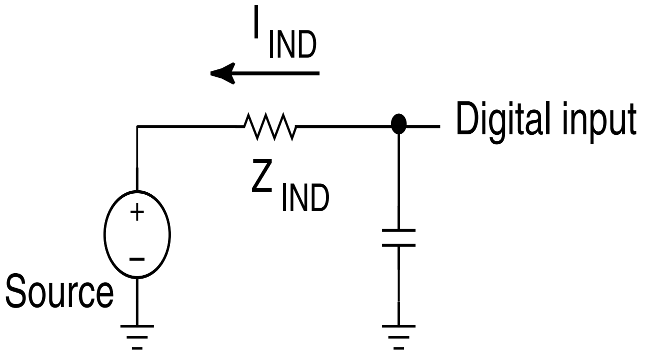
Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
I_{IND}	Input leakage current, digital pins					4, 5
	• $V_{DD} < V_{IN} < 5.5$ V	—	1	50	μA	
Z_{IND}	Input impedance examples, digital pins					4, 7
	• $V_{DD} = 3.6$ V	—	—	48	kΩ	
	• $V_{DD} = 3.0$ V	—	—	55	kΩ	
	• $V_{DD} = 2.5$ V	—	—	57	kΩ	
	• $V_{DD} = 1.7$ V	—	—	85	kΩ	
R_{PU}	Internal pullup resistors	20	35	50	kΩ	8
R_{PD}	Internal pulldown resistors	20	35	50	kΩ	9

1. Typical values characterized at 25°C and VDD = 3.6 V unless otherwise noted.
2. Open drain outputs must be pulled to V_{DD}.
3. Analog pins are defined as pins that do not have an associated general purpose I/O port function.
4. Digital pins have an associated GPIO port function and have 5V tolerant inputs, except EXTAL and XTAL.
5. Internal pull-up/pull-down resistors disabled.
6. Characterized, not tested in production.
7. Examples calculated using V_{IL} relation, V_{DD}, and max I_{IND}: $Z_{IND}=V_{IL}/I_{IND}$. This is the impedance needed to pull a high signal to a level below V_{IL} due to leakage when $V_{IL} < V_{IN} < V_{DD}$. These examples assume signal source low = 0 V.
8. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}
9. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}



5.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 100 MHz
- Bus clock = 50 MHz
- FlexBus clock = 50 MHz
- Flash clock = 25 MHz
- MCG mode: FEI

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip. • V_{DD} slew rate ≥ 5.7 kV/s • V_{DD} slew rate < 5.7 kV/s	 — —	 300 1.7 V / (V_{DD} slew rate)	μs	1
	• VLLS1 → RUN	—	134	μs	
	• VLLS2 → RUN	—	96	μs	
	• VLLS3 → RUN	—	96	μs	
	• LLS → RUN	—	6.2	μs	
	• VLPS → RUN	—	5.9	μs	
	• STOP → RUN	—	5.9	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash • @ 1.8V • @ 3.0V	 — —	 45 47	 70 72	 mA mA	2

I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash
	• @ 1.8V
	• @ 3.0V
	  • @ 25°C
	  • @ 125°C
		
		—
		
		—
		—
			
			61
			
			63
			72
				
				85
				
				71
				87
					
					mA
					
					mA
					mA
						3, 4

I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	35	—	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	15	—	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	N/A	—	mA	6

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	N/A	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	—	N/A	—	mA	8
I_{DD_STOP}	Stop mode current at 3.0 V					
	• @ –40 to 25°C	—	0.59	1.4	mA	
	• @ 70°C	—	2.26	7.9	mA	
	• @ 105°C	—	5.94	19.2	mA	
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	• @ –40 to 25°C	—	93	435	µA	
	• @ 70°C	—	520	2000	µA	
	• @ 105°C	—	1350	4000	µA	
I_{DD_LLS}	Low leakage stop mode current at 3.0 V					9
	• @ –40 to 25°C	—	4.8	20	µA	
	• @ 70°C	—	28	68	µA	
	• @ 105°C	—	126	270	µA	
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					9
	• @ –40 to 25°C	—	3.1	8.9	µA	
	• @ 70°C	—	17	35	µA	
	• @ 105°C	—	82	148	µA	
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					
	• @ –40 to 25°C	—	2.2	5.4	µA	
	• @ 70°C	—	7.1	12.5	µA	
	• @ 105°C	—	41	125	µA	
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	• @ –40 to 25°C	—	2.1	7.6	µA	
	• @ 70°C	—	6.2	13.5	µA	
	• @ 105°C	—	30	46	µA	
I_{DD_VBAT}	Average current with RTC and 32kHz disabled at 3.0 V					
	• @ –40 to 25°C	—	0.33	0.39	µA	
	• @ 70°C	—	0.60	0.78	µA	
	• @ 105°C	—	1.97	2.9	µA	

Table continues on the next page...

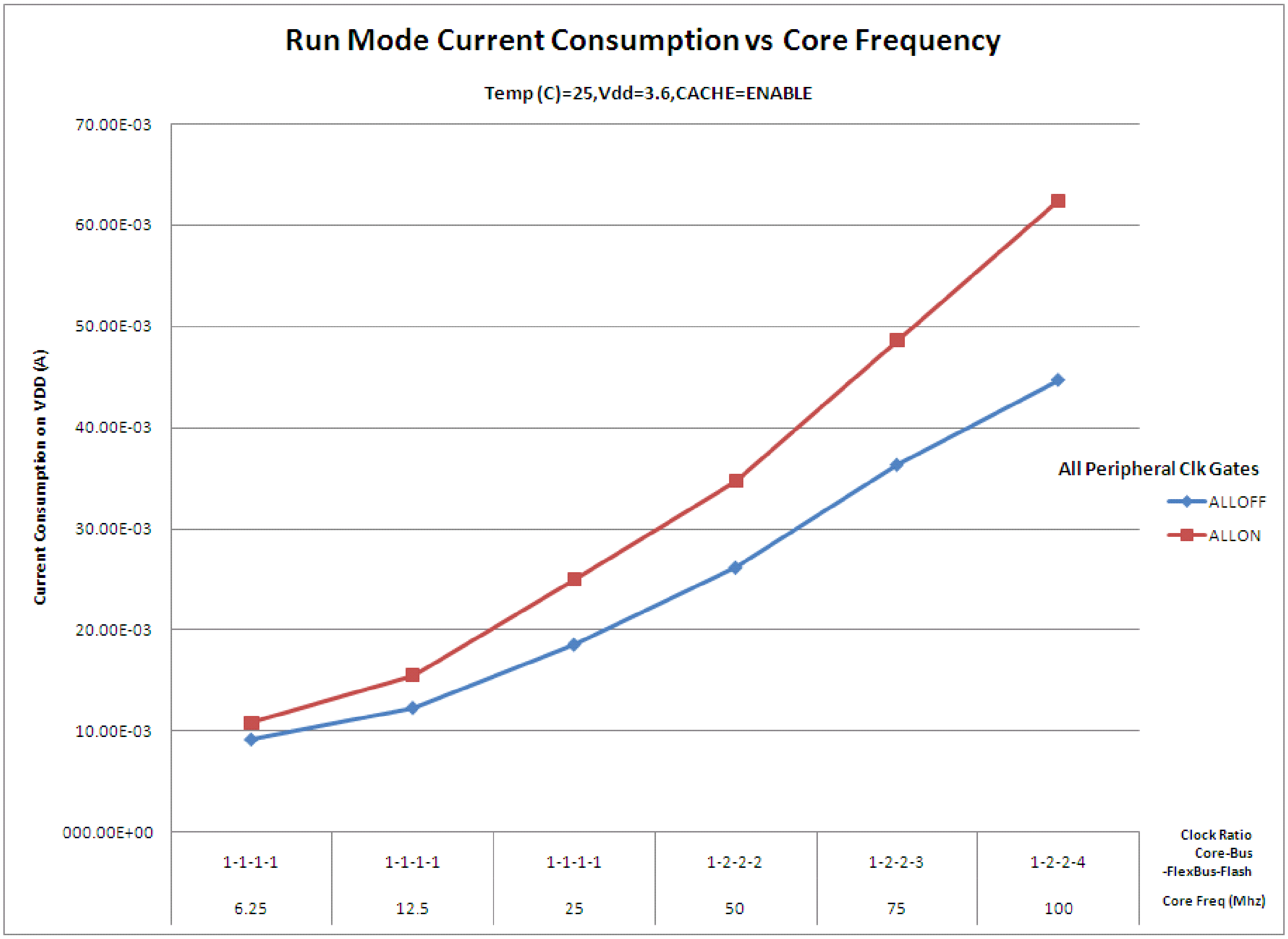


Figure 2. Run mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors as measured on 144LQFP and 144MAPBGA packages

Symbol	Description	Frequency band (MHz)	144LQFP	144MAPBGA	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	23	12	dBμV	1 , 2
V_{RE2}	Radiated emissions voltage, band 2	50–150	27	24	dBμV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	28	27	dBμV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	14	11	dBμV	
V_{RE_IEC}	IEC level	0.15–1000	K	K	—	2, 3

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 Debug trace timing specifications

Table 12. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
T_{cyc}	Clock period	Frequency dependent		MHz
T_{wl}	Low pulse width	2	—	ns
T_{wh}	High pulse width	2	—	ns
T_r	Clock and data rise time	—	3	ns
T_f	Clock and data fall time	—	3	ns
T_s	Data setup	3	—	ns
T_h	Data hold	2	—	ns

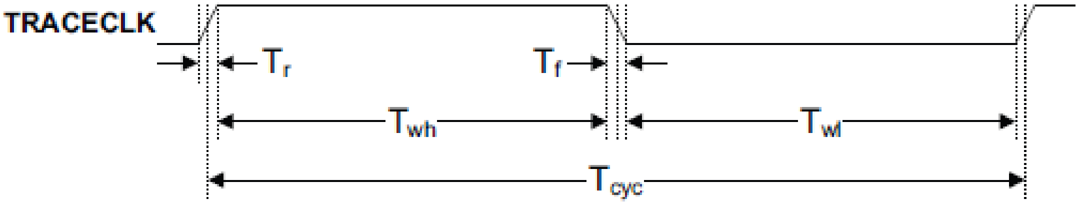


Figure 3. TRACE_CLKOUT specifications

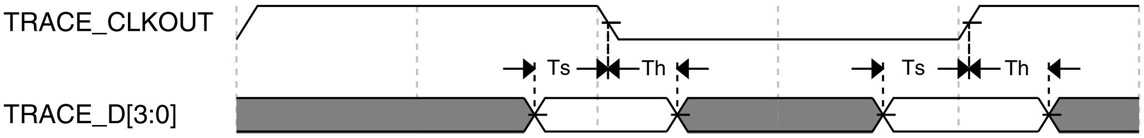


Figure 4. Trace data specifications

Table 17. Oscillator frequency specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.3.3 32 kHz Oscillator Electrical Characteristics

This section describes the module electrical characteristics.

6.3.3.1 32 kHz oscillator DC electrical specifications

Table 18. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{BAT}	Supply voltage	1.71	—	3.6	V
R_F	Internal feedback resistor	—	100	—	MΩ
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp}[1]	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.3.2 32 kHz oscillator frequency specifications

Table 19. 32 kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$f_{ec\_extal32}$	Externally provided input clock frequency	—	32.768	—	kHz	2
$v_{ec\_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT}.

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 20. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk256k}$	Erase Block high-voltage time for 256 KB	—	416	3616	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 21. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Read 1s Block execution time					
$t_{rd1blk256k}$	• 256 KB program/data flash	—	—	1.7	ms	
$t_{rd1sec2k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1

Table continues on the next page...

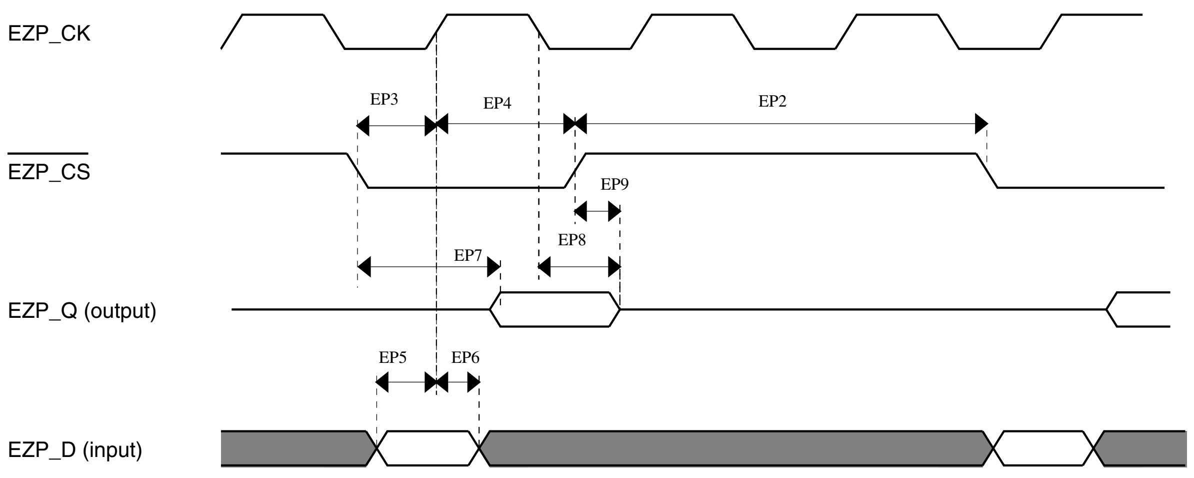


Figure 9. EzPort Timing Diagram

6.4.3 Flexbus Switching Specifications

All processor bus timings are synchronous; input setup/hold and output delay are given in respect to the rising edge of a reference clock, FB_CLK. The FB_CLK frequency may be the same as the internal system bus frequency or an integer divider of that frequency.

The following timing numbers indicate when data is latched or driven onto the external bus, relative to the Flexbus output clock (FB_CLK). All other timing relationships can be derived from these values.

Table 25. Flexbus limited voltage range switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	FB_CLK	MHz	
FB1	Clock period	20	—	ns	
FB2	Address, data, and control output valid	—	11.5	ns	1
FB3	Address, data, and control output hold	0.5	—	ns	1
FB4	Data and $\overline{\text{FB\_TA}}$ input setup	8.5	—	ns	2
FB5	Data and $\overline{\text{FB\_TA}}$ input hold	0.5	—	ns	2

1. Specification is valid for all FB_AD[31:0], $\overline{\text{FB\_BE/BWE}n}$, $\overline{\text{FB\_CS}n}$, $\overline{\text{FB\_OE}}$, FB_R/$\overline{\text{W}}$,$\overline{\text{FB\_TBST}}$, FB_TSIZ[1:0], FB_ALE, and $\overline{\text{FB\_TS}}$.

2. Specification is valid for all FB_AD[31:0] and FB_TA.

Table 26. Flexbus full voltage range switching specifications

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	
	Frequency of operation	—	FB_CLK	MHz	
FB1	Clock period	1/FB_CLK	—	ns	
FB2	Address, data, and control output valid	—	13.5	ns	1
FB3	Address, data, and control output hold	0	—	ns	1
FB4	Data and FB_TA input setup	13.7	—	ns	2
FB5	Data and FB_TA input hold	0.5	—	ns	2

1. Specification is valid for all FB_AD[31:0], FB_BE/BWE*n*, FB_CS*n*, FB_OE, FB_R/W,FB_TBST, FB_TSIZ[1:0], FB_ALE, and FB_TS.
2. Specification is valid for all FB_AD[31:0] and FB_TA.

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 27 and Table 28 are achievable on the differential pins ADCx_DP0, ADCx_DM0, ADCx_DP1, ADCx_DM1, ADCx_DP3, and ADCx_DM3.

The ADCx_DP2 and ADCx_DM2 ADC inputs are connected to the PGA outputs and are not direct device pins. Accuracy specifications for these pins are defined in Table 29 and Table 30.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 27. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD} - V_{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS} - V_{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage	• 16-bit differential mode • All other modes	VREFL VREFL	— —	31/32 * VREFH VREFH	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5

Table continues on the next page...

Table 31. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}-0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

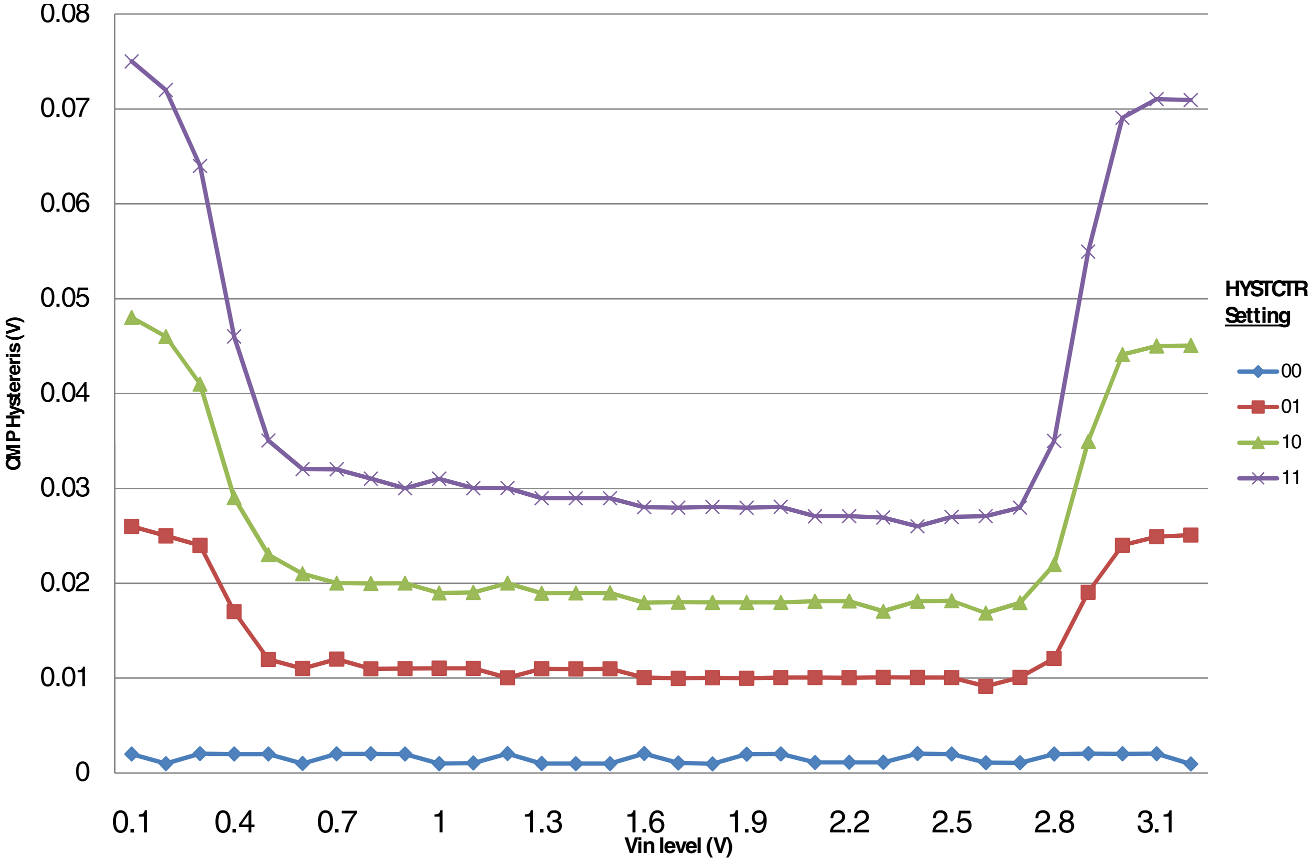


Figure 15. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=0)

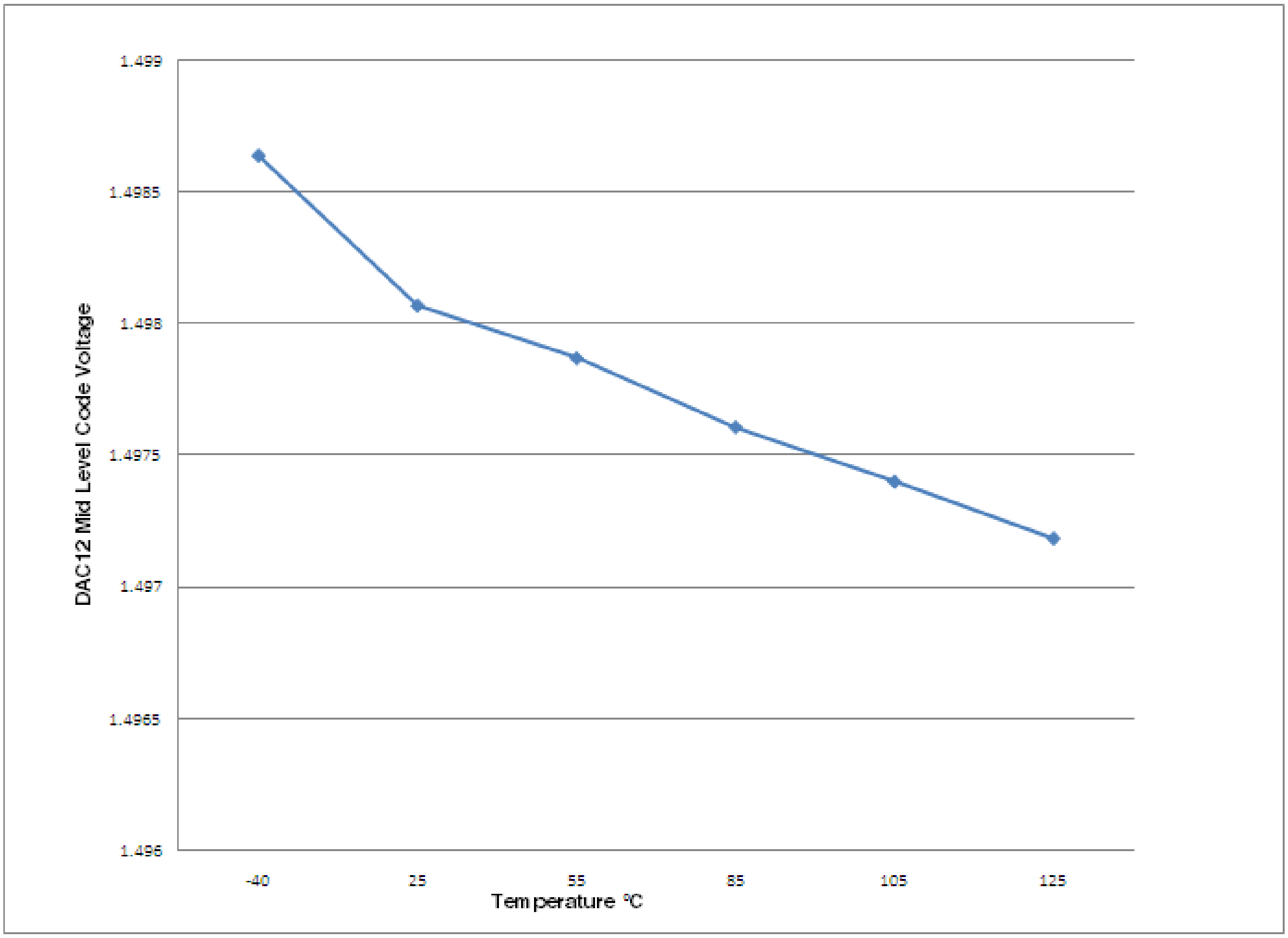


Figure 18. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 34. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	100		nF	1, 2

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
2. The load capacitance should not exceed +/-25% of the nominal specified C_L value over the operating temperature range of the device.

6. C_b = total capacitance of the one bus line in pF.

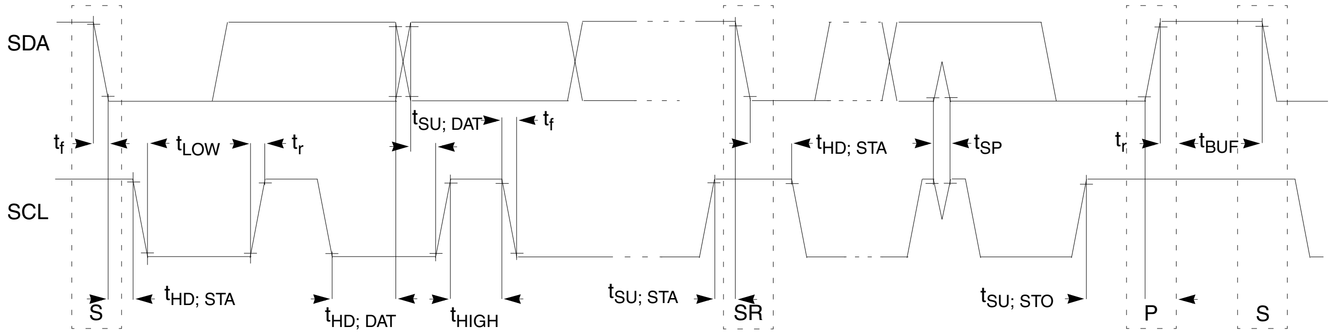


Figure 23. Timing definition for fast and standard mode devices on the I^{2}C bus

6.8.5 UART switching specifications

See General switching specifications.

6.8.6 SDHC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

Table 43. SDHC switching specifications

Num	Symbol	Description	Min.	Max.	Unit
	Card input clock				
SD1	fpp	Clock frequency (low speed)	0	400	kHz
	fpp	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	fpp	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f_{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t_{WL}	Clock low time	7	—	ns
SD3	t_{WH}	Clock high time	7	—	ns
SD4	t_{TLH}	Clock rise time	—	3	ns
SD5	t_{THL}	Clock fall time	—	3	ns
	SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)				
SD6	t_{OD}	SDHC output delay (output valid)	-5	8.3	ns
	SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)				
SD7	t_{ISU}	SDHC input setup time	5	—	ns
SD8	t_{IH}	SDHC input hold time	0	—	ns

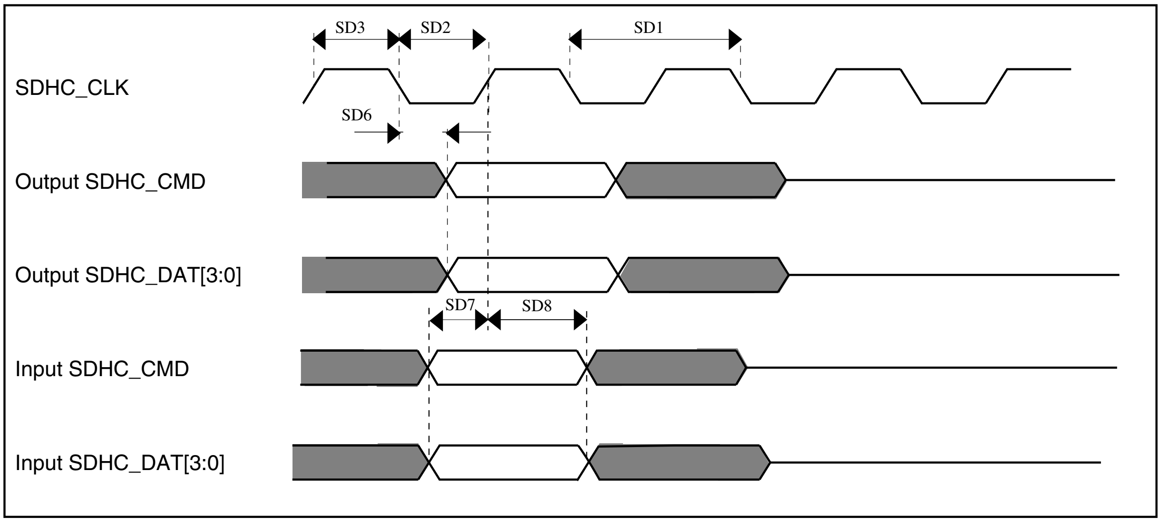


Figure 24. SDHC timing

6.8.7 I^2S switching specifications

This section provides the AC timings for the I^2S in master (clocks driven) and slave modes (clocks input). All timings are given for non-inverted serial clock polarity (TCR[TSCKP] = 0, RCR[RSCKP] = 0) and a non-inverted frame sync (TCR[TFSI] = 0, RCR[RFSI] = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timings remain valid by inverting the clock signal (I2S_BCLK) and/or the frame sync (I2S_FS) shown in the figures below.

Table 44. I^2S master mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S1	I2S_MCLK cycle time	2 x t_{SYS}		ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_BCLK cycle time	5 x t_{SYS}	—	ns
S4	I2S_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_BCLK to I2S_FS output valid	—	15	ns
S6	I2S_BCLK to I2S_FS output invalid	-2.5	—	ns
S7	I2S_BCLK to I2S_TXD valid	—	15	ns
S8	I2S_BCLK to I2S_TXD invalid	-3	—	ns
S9	I2S_RXD/I2S_FS input setup before I2S_BCLK	20	—	ns
S10	I2S_RXD/I2S_FS input hold after I2S_BCLK	0	—	ns

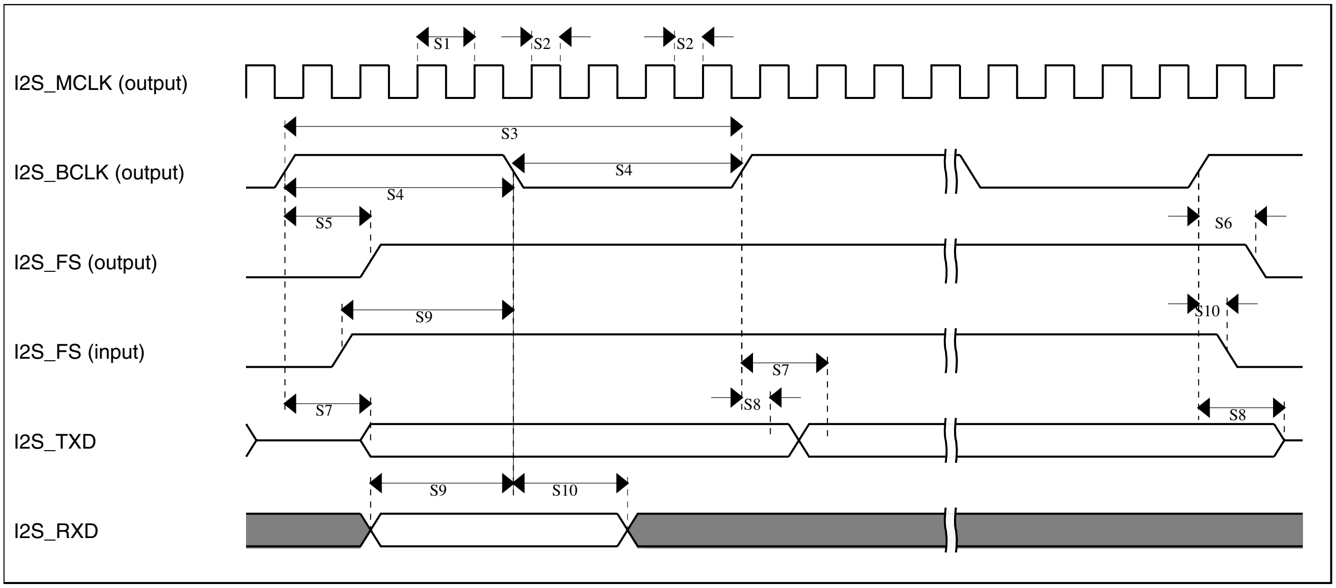


Figure 25. I^{2}S timing — master mode

Table 45. I^{2}S slave mode timing (limited voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S11	I2S_BCLK cycle time (input)	8 x t_{SYS}	—	ns
S12	I2S_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_FS input setup before I2S_BCLK	10	—	ns
S14	I2S_FS input hold after I2S_BCLK	3	—	ns
S15	I2S_BCLK to I2S_TXD/I2S_FS output valid	—	20	ns
S16	I2S_BCLK to I2S_TXD/I2S_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_BCLK	2	—	ns

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 48. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DDTSI}	Operating voltage	1.71	—	3.6	V	
C_{ELE}	Target electrode capacitance range	1	20	500	pF	1
f_{REFmax}	Reference oscillator frequency	—	5.5	12.7	MHz	2
f_{ELEmax}	Electrode oscillator frequency	—	0.5	4.0	MHz	3
C_{REF}	Internal reference capacitor	0.5	1	1.2	pF	
V_{DELTA}	Oscillator delta voltage	100	600	760	mV	4
I_{REF}	Reference oscillator current source base current • 1uA setting (REFCHRG=0) • 32uA setting (REFCHRG=31)	— —	1.133 36	1.5 50	μA	3 , 5
I_{ELE}	Electrode oscillator current source base current • 1uA setting (EXTCHRG=0) • 32uA setting (EXTCHRG=31)	— —	1.133 36	1.5 50	μA	3 , 6
Pres5	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	7
Pres20	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	8
Pres100	Electrode capacitance measurement precision	—	8.3333	38400	fF/count	9
MaxSens	Maximum sensitivity	0.003	12.5	—	fF/count	10
Res	Resolution	—	—	16	bits	
T_{Con20}	Response time @ 20 pF	8	15	25	μs	11
I_{TSI_RUN}	Current added in run mode	—	55	—	μA	
I_{TSI_LP}	Low power mode current adder	—	1.3	2.5	μA	12

1. The TSI module is functional with capacitance values outside this range. However, optimal performance is not guaranteed.
2. CAPTRM=7, DELVOL=7, and fixed external capacitance of 20 pF.
3. CAPTRM=0, DELVOL=2, and fixed external capacitance of 20 pF.
4. CAPTRM=0, EXTCHRG=9, and fixed external capacitance of 20 pF.
5. The programmable current source value is generated by multiplying the SCANC[REFCHRG] value and the base current.
6. The programmable current source value is generated by multiplying the SCANC[EXTCHRG] value and the base current.
7. Measured with a 5 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 8; Iext = 16.
8. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 128, NSCN = 2; Iext = 16.
9. Measured with a 20 pF electrode, reference oscillator frequency of 10 MHz, PS = 16, NSCN = 3; Iext = 16.
10. Sensitivity defines the minimum capacitance change when a single count from the TSI module changes, it is equal to (C_{ref} * I_{ext})/(I_{ref} * PS * NSCN). Sensitivity depends on the configuration used. The typical value listed is based on the following configuration: Iext = 5 μA, EXTCHRG = 4, PS = 128, NSCN = 2, $I_{ref} = 16$ μA, REFCHRG = 15, C_{ref} = 1.0 pF. The minimum sensitivity describes the smallest possible capacitance that can be measured by a single count (this is the best sensitivity but is described as a minimum because it's the smallest number). The minimum sensitivity parameter is based on the following configuration: $I_{ext} = 1$ μA, EXTCHRG = 0, PS = 128, NSCN = 32, $I_{ref} = 32$ μA, REFCHRG = 31, C_{ref}= 0.5 pF
11. Time to do one complete measurement of the electrode. Sensitivity resolution of 0.0133 pF, PS = 0, NSCN = 0, 1 electrode, DELVOL = 2, EXTCHRG = 15.
12. CAPTRM=7, DELVOL=2, REFCHRG=0, EXTCHRG=4, PS=7, NSCN=0F, LPSCNITV=F, LPO is selected (1 kHz), and fixed external capacitance of 20 pF. Data is captured with an average of 7 periods window.

144 LQFP	144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
60	K8	PTA8	ADC0_SE11	ADC0_SE11	PTA8		FTM1_CH0			FTM1_QD_PHA	TRACE_D2	
61	L8	PTA9	DISABLED		PTA9		FTM1_CH1			FTM1_QD_PHB	TRACE_D1	
62	M9	PTA10	DISABLED		PTA10		FTM2_CH0			FTM2_QD_PHA	TRACE_D0	
63	L9	PTA11	DISABLED		PTA11		FTM2_CH1			FTM2_QD_PHB		
64	K9	PTA12	CMP2_IN0	CMP2_IN0	PTA12	CAN0_TX	FTM1_CH0			I2S0_TXD	FTM1_QD_PHA	
65	J9	PTA13/LLWU_P4	CMP2_IN1	CMP2_IN1	PTA13/LLWU_P4	CAN0_RX	FTM1_CH1			I2S0_TX_FS	FTM1_QD_PHB	
66	L10	PTA14	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_TX_BCLK		
67	L11	PTA15	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD		
68	K10	PTA16	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_b			I2S0_RX_FS		
69	K11	PTA17	ADC1_SE17	ADC1_SE17	PTA17	SPI0_SIN	UART0_RTS_b			I2S0_MCLK	I2S0_CLKIN	
70	E8	VDD	VDD	VDD								
71	G8	VSS	VSS	VSS								
72	M12	PTA18	EXTAL	EXTAL	PTA18		FTM0_FLT2	FTM_CLKIN0				
73	M11	PTA19	XTAL	XTAL	PTA19		FTM1_FLT0	FTM_CLKIN1		LPT0_ALT1		
74	L12	RESET_b	RESET_b	RESET_b								
75	K12	PTA24	DISABLED		PTA24					FB_A29		
76	J12	PTA25	DISABLED		PTA25					FB_A28		
77	J11	PTA26	DISABLED		PTA26					FB_A27		
78	J10	PTA27	DISABLED		PTA27					FB_A26		
79	H12	PTA28	DISABLED		PTA28					FB_A25		
80	H11	PTA29	DISABLED		PTA29					FB_A24		
81	H10	PTB0/LLWU_P5	ADC0_SE8/ADC1_SE8/TSI0_CH0	ADC0_SE8/ADC1_SE8/TSI0_CH0	PTB0/LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_PHA		
82	H9	PTB1	ADC0_SE9/ADC1_SE9/TSI0_CH6	ADC0_SE9/ADC1_SE9/TSI0_CH6	PTB1	I2C0_SDA	FTM1_CH1			FTM1_QD_PHB		
83	G12	PTB2	ADC0_SE12/TSI0_CH7	ADC0_SE12/TSI0_CH7	PTB2	I2C0_SCL	UART0_RTS_b			FTM0_FLT3		
84	G11	PTB3	ADC0_SE13/TSI0_CH8	ADC0_SE13/TSI0_CH8	PTB3	I2C0_SDA	UART0_CTS_b			FTM0_FLT0		
85	G10	PTB4	ADC1_SE10	ADC1_SE10	PTB4					FTM1_FLT0		
86	G9	PTB5	ADC1_SE11	ADC1_SE11	PTB5					FTM2_FLT0		
87	F12	PTB6	ADC1_SE12	ADC1_SE12	PTB6				FB_AD23			
88	F11	PTB7	ADC1_SE13	ADC1_SE13	PTB7				FB_AD22			